

# isc Silicon NPN Power Transistor

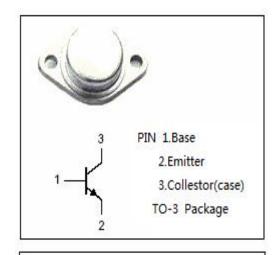
2SD113

## DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V (Min)
- · High Power Dissipation
- · High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

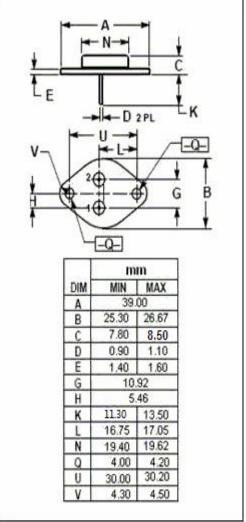
#### **APPLICATIONS**

- · Audio power amplifier, power switching applications.
- · DC-DC converter and regulator applications.



## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage 100		V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
lc	Collector Current-Continuous 30		Α
Ι <sub>Ε</sub>	Emitter Current-Continuous 30		Α
I <sub>B</sub>	Base Current-Continuous 5		Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25 ℃		W
T <sub>j</sub>	Junction Temperature	150	
T <sub>stg</sub>	Storage Temperature Range -65~150		$^{\circ}$





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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

			TC-20 O difference opening							
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT				
V <sub>(BR)CEO</sub>	Collector- Emitte Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = ∞	80			V				
V <sub>(BR)EBO</sub>	Emitte - Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	10			V				
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3A			1.5	V				
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3A			2.5	V				
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 50V; I <sub>E</sub> = 0			2	mA				
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 10V; I <sub>C</sub> = 0			50	mA				
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	50		300					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 15A; V <sub>CE</sub> = 5V	10							
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 50V; f <sub>test</sub> = 1.0MHz		400		pF				
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V		1.5		MHz				

## h<sub>FE-1</sub> Classifications

0	Y		
50-150	100-300		

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